ELSEVIER

Journal of Crystal Growth 213 (2000) 421–425

JOURNAL OF CRYSTAL GROWTH

www.elsevier.nl/locate/jcrysgro

Author index

Abril, E.J., see Villar, C. 213 (2000) 214
Aguilar, M., see Villar, C. 213 (2000) 214
Ahn, H.S., see Barnes, M.C. 213 (2000) 83
Akaishi, M., see Shaji Kumar, M.D. 213 (2000) 203
Akaishi, M., see Sun, L. 213 (2000) 411
Amberg, G., see Tönhardt, R. 213 (2000) 161
Arora, B.M., see Sharma, T.K. 213 (2000) 241
Arora, B.M., see Chandvankar, S.S. 213 (2000) 250

Barnes, M.C., D.-Y. Kim, H.S. Ahn, C.O. Lee and N.M. Hwang, Deposition mechanism of gold by thermal evaporation: approach by charged cluster model 213 (2000) 83
Bartosch, K., see Rauls, M. 213 (2000) 116
Behr, G., see Bitterlich, H. 213 (2000) 319
Bitterlich, H., W. Löser, G. Behr, G. Graw, W. Yang-Bitterlich, U. Krämer and L. Schultz, Single-crystal growth of $Tb_{0.4}Y_{0.6}Ni_2B_2C$ compounds by the floating-zone method 213 (2000) 319
Boleslawski, M.P., see Zhang, L. 213 (2000) 1
Botha, J.R., see Wagener, M.C. 213 (2000) 51
Bouropoulos, N.Ch. and P.G. Koutsoukos, Spontaneous precipitation of struvite from aqueous solutions 213 (2000) 381

Cao, Y.G., X.L. Chen, Y.C. Lan, J.Y. Li, Y.P. Xu, T. Xu, Q.L. Liu and J.K. Liang, Blue emission and Raman scattering spectrum from AlN nanocrystalline powders 213 (2000) 198
Cao, Y.G., see Li, J.Y. 213 (2000) 408
Chandrasekaran, K.S., see Chandvankar, S.S. 213 (2000) 250
Chandvankar, S.S., T.K. Sharma, A.P. Shah, K.S. Chandrasekaran, B.M. Arora, A.K. Kapoor, D. Verma and B.B. Sharma, Indium thallium phosphide: experiments versus predictions 213 (2000) 250
Chen, H., see Zhang, S. 213 (2000) 415
Chen, P., S.Y. Xie, Z.Z. Chen, Y.G. Zhou, B. Shen, R. Zhang, Y.D. Zheng, J.M. Zhu, M. Wang, X.S. Wu, S.S. Jiang and D. Feng, Deposition and crystallization of amorphous GaN buffer layers on Si(1 1 1) substrates 213 (2000) 27
Chen, X.L., see Cao, Y.G. 213 (2000) 198
Chen, X.L., see Li, J.Y. 213 (2000) 408
Chen, Z.Z., see Chen, P. 213 (2000) 27
Cheng, B., see Li, D. 213 (2000) 308
Cheng, Z., see Zhang, S. 213 (2000) 415
Chian, C.H., see Lan, C.W. 213 (2000) 395
Choi, Y., see Kim, C. 213 (2000) 235

Dalas, E., see Pierri, E. 213 (2000) 93
Ding, D., see Liu, H.Y. 213 (2000) 193

Fainberg, J., see Frank, Ch. 213 (2000) 10
Fan, T.W., J.J. Qian, J. Wu, L.Y. Lin and J. Yuan, Tentative analysis of Swirl defects in silicon crystals 213 (2000) 276
Fatemi, M., see Jernigan, G.G. 213 (2000) 299
Feigelson, R.S., see Petrosyan, A.M. 213 (2000) 103
Feng, D., see Chen, P. 213 (2000) 27
Feth, S., see Su, C.-H. 213 (2000) 267
Frank, Ch., K. Jacob, M. Neubert, P. Rudolph, J. Fainberg and G. Müller, Temperature field simulation and correlation to the structural quality of semi-insulating GaAs crystals grown by the vapour pressure controlled Czochralski method (VCz) 213 (2000) 10
Fuenzalida, V.M., Pulsed deposition and postnucleation: model for the average cluster size as a function of the number of pulses 213 (2000) 157
Fujita, K., see Villar, C. 213 (2000) 214

George, M.A., see Su, C.-H. 213 (2000) 267
Gheorghies, C., The electrolytic preparation and physical characterization of $ZrTiO_4$ films 213 (2000) 112
Gokhale, M.R., see Sharma, T.K. 213 (2000) 241
Graw, G., see Bitterlich, H. 213 (2000) 319
Gribenyukov, A.I., see Verozubova, G.A. 213 (2000) 334

0022-0248/00/$ - see front matter © 2000 Elsevier Science B.V. All rights reserved.
PII: S0022-0248(00)00476-0

Grousson, R., see Wang, X.-L. 213 (2000) 19
Gu, S.L., see Zhang, L. 213 (2000) 1
Guo, X.J., see Wen, C.-Y. 213 (2000) 150

Han, J., see Zhang, S. 213 (2000) 415
Harris, S., Surfactant-moderated growth on a vicinal surface 213 (2000) 75
Härtwig, J., see Morelhão, S.L. 213 (2000) 288
Hayakawa, Y., Y. Okano, A. Hirata, N. Imaishi, Y. Kumagiri, X. Zhong, X. Xie, B. Yuan, F. Wu, H. Liu, T. Yamaguchi and M. Kumagawa, Experimental and numerical investigations on dissolution and recrystallization processes of GaSb/InSb/GaSb under microgravity and terrestrial conditions 213 (2000) 40
He, Y., see Su, G. 213 (2000) 99
Hirata, A., see Hayakawa, Y. 213 (2000) 40
Hofmann, L., A. Knauer, I. Rechenberg, U. Zeimer and M. Weyers, Comparison of binary and ternary growth over trenches using MOVPE 213 (2000) 229
Hofmeister, H., see Nepijko, S.A. 213 (2000) 129
Hoshikawa, K., see Huang, X. 213 (2000) 283
Huang, C., see Li, D. 213 (2000) 308
Huang, J.H., see Wen, C.-Y. 213 (2000) 150
Huang, W.D., S. Naritsuka and T. Nishinaga, Vertical Bridgman growth of $Al_xGa_{1-x}Sb$ single crystals 213 (2000) 207
Huang, X., T. Taishi, I. Yonenaga and K. Hoshikawa, Dislocation-free B-doped Si crystal growth without Dash necking in Czochralski method: influence of B concentration 213 (2000) 283
Hwang, D.-H., B.-Y. Lee, H.-D. Yoo and O.-J. Kwon, Anomalous oxygen precipitation near the vacancy and interstitial boundary in CZ-Si wafers 213 (2000) 57
Hwang, N.M., see Jeon, J.-D. 213 (2000) 79
Hwang, N.M., see Barnes, M.C. 213 (2000) 83

Imaishi, N., see Hayakawa, Y. 213 (2000) 40

Jacob, K., see Frank, Ch. 213 (2000) 10
Jansson, U., see Talyzin, A.V. 213 (2000) 63
Jeon, J.-D., C.J. Park, D.-Y. Kim and N.M. Hwang, Experimental confirmation of charged carbon clusters in the hot filament diamond reactor 213 (2000) 79
Jernigan, G.G., C.L. Silvestre, M. Fatemi, M.E. Twigg and P.E. Thompson, Composition and morphology of SiGe alloys grown on Si(100) using an Sb surfactant 213 (2000) 299
Jiang, R., see Su, G. 213 (2000) 99
Jiang, S.S., see Chen, P. 213 (2000) 27
Jiang, W.H., see Liu, H.Y. 213 (2000) 193
Jiang, X., see Xia, Y. 213 (2000) 328
Jimenez-Sandoval, S., see Rodriguez, M.E. 213 (2000) 259

Kang, K.Y., see Lee, J.J. 213 (2000) 33
Kang, T.W., see Lee, J.J. 213 (2000) 33
Kapoor, A.K., see Chandvankar, S.S. 213 (2000) 250
Karapetyan, H.A., see Petrosyan, A.M. 213 (2000) 103
Katz, J.L., see Parsiegla, K.I. 213 (2000) 368
Kim, C., M. Yang, W. Lee, J. Yi, S. Kim, Y. Choi, T.-K. Yoo and S.T. Kim, Formation and characteristics of inversion domain in GaN grown by hydride vapor-phase epitaxy 213 (2000) 235
Kim, D.-Y., see Jeon, J.-D. 213 (2000) 79
Kim, D.-Y., see Barnes, M.C. 213 (2000) 83
Kim, H.S., see Lee, J.J. 213 (2000) 33
Kim, K.H., see Lee, J.J. 213 (2000) 33
Kim, S., see Kim, C. 213 (2000) 235
Kim, S.T., see Kim, C. 213 (2000) 235
Kind, M., see Rauls, M. 213 (2000) 116
Knauer, A., see Hofmann, L. 213 (2000) 229
Korotkova, V.V., see Verozubova, G.A. 213 (2000) 334
Koutsoukos, P.G., see Bouropoulos, N.Ch. 213 (2000) 381
Krämer, U., see Bitterlich, H. 213 (2000) 319
Kuch, St., see Rauls, M. 213 (2000) 116
Kuech, T.F., see Zhang, L. 213 (2000) 1
Kumagawa, M., see Hayakawa, Y. 213 (2000) 40
Kumagiri, Y., see Hayakawa, Y. 213 (2000) 40
Kwon, O.-J., see Hwang, D.-H. 213 (2000) 57

Lacmann, R., see Rauls, M. 213 (2000) 116
Lan, C.W., M.C. Liang and C.H. Chian, Suppressing three-dimensional unsteady flows in vertical zone-melting by steady ampoule rotation 213 (2000) 395
Lan, Y.C., see Cao, Y.G. 213 (2000) 198
Lan, Y.C., see Li, J.Y. 213 (2000) 408
Lee, B.-Y., see Hwang, D.-H. 213 (2000) 57
Lee, C.O., see Barnes, M.C. 213 (2000) 83
Lee, J.J., Y.S. Park, C.S. Yang, H.S. Kim, K.H. Kim, K.Y. Kang, T.W. Kang, S.H. Park and J.Y. Lee, MBE growth of wurtzite GaN on $LaAlO_3$(100) substrate 213 (2000) 33
Lee, J.Y., see Lee, J.J. 213 (2000) 33
Lee, W., see Kim, C. 213 (2000) 235
Lehoczky, S.L., see Su, C.-H. 213 (2000) 267
Leitch, A.W.R., see Wagener, M.C. 213 (2000) 51
Leonartz, K., see Suk, M.-J. 213 (2000) 141
Li, D., C. Huang, B. Cheng, H. Wang, Z. Yu, C. Zhang, J. Yu and Q. Wang, Effect of low-temperature SiGe interlayer on the growth of relaxed SiGe 213 (2000) 308
Li, J.Y., see Cao, Y.G. 213 (2000) 198
Li, J.Y., X.L. Chen, Z.Y. Qiao, Y.G. Cao and Y.C. Lan, Formation of GaN nanorods by a sublimation method 213 (2000) 408

Li, Z., see Su, G. 213 (2000) 99
Liang, J.K., see Cao, Y.G. 213 (2000) 198
Liang, M.C., see Lan, C.W. 213 (2000) 395
Lin, L.Y., see Fan, T.W. 213 (2000) 276
Liu, H., see Hayakawa, Y. 213 (2000) 40
Liu, H.Y., X.D. Wang, B. Xu, D. Ding, W.H. Jiang, J. Wu and Z.G. Wang, Effect of In-mole-fraction in InGaAs overgrowth layer on self-assembled InAs/GaAs quantum dots 213 (2000) 193
Liu, Q.L., see Cao, Y.G. 213 (2000) 198
López, M., see Villar, C. 213 (2000) 214
Löser, W., see Bitterlich, H. 213 (2000) 319

MacManus-Driscoll, J.L., see Qi, X. 213 (2000) 312
Meera, K., see Rajesh, N.P. 213 (2000) 389
Meier, D.L., see Morelhão, S.L. 213 (2000) 288
Mersmann, A., see Rauls, M. 213 (2000) 116
Mizoguchi, M., see Watanabe, K. 213 (2000) 135
Morelhão, S.L., J. Härtwig and D.L. Meier, Dislocations in dendritic web silicon 213 (2000) 288
Morishima, Y., see Wang, T. 213 (2000) 188
Müller, G., see Frank, Ch. 213 (2000) 10

Naoi, N., see Wang, T. 213 (2000) 188
Naritsuka, S., see Huang, W.D. 213 (2000) 207
Narlikar, A.V., see Singh, R. 213 (2000) 70
Nepijko, S.A., H. Hofmeister, H. Sack-Kongehl and R. Schlögl, Multiply twinned particles beyond the icosahedron 213 (2000) 129
Neubert, M., see Frank, Ch. 213 (2000) 10
Nishinaga, T., see Huang, W.D. 213 (2000) 207
Nishizawa, J.-i., see Oyama, Y. 213 (2000) 221

Ogura, M., see Wang, X.-L. 213 (2000) 19
Okano, Y., see Hayakawa, Y. 213 (2000) 40
Oyama, Y., J.-i. Nishizawa, K. Seo and K. Suto, X-ray multi-crystal diffractometry analysis of heavily Te-doped GaAs grown by intermittent injection of $TEGa/AsH_3$ in ultra high vacuum 213 (2000) 221

Palosz, W., see Su, C.-H. 213 (2000) 267
Park, C.J., see Jeon, J.-D. 213 (2000) 79
Park, S.H., see Lee, J.J. 213 (2000) 33
Park, Y.S., see Lee, J.J. 213 (2000) 33
Parsiegla, K.I. and J.L. Katz, Calcite growth inhibition by copper(II). II. Effect of solution composition 213 (2000) 368
Pérez Bueno, J.J., see Rodriguez, M.E. 213 (2000) 259
Petrosyan, A.M., R.P. Sukiasyan, H.A. Karapetyan, S.S. Terzyan and R.S. Feigelson, Growth and investigation of new non-linear optical crystals of LAP family 213 (2000) 103
Pierri, E., D. Tsamouras and E. Dalas, Ferric phosphate precipitation in aqueous media 213 (2000) 93
Potapenko, S.Yu., see Robey, H.F. 213 (2000) 340
Potapenko, S.Yu., see Robey, H.F. 213 (2000) 355

Qi, X. and J.L. MacManus-Driscoll, Liquid-phase epitaxial growth of $REBa_2Cu_3O_{7-\delta}$ (RE = Y, Yb, Er) thick films at reduced temperatures 213 (2000) 312
Qian, J.J., see Fan, T.W. 213 (2000) 276
Qiao, Z.Y., see Li, J.Y. 213 (2000) 408

Raghavan, P.S., see Rajesh, N.P. 213 (2000) 389
Rajesh, N.P., K. Meera, K. Srinivasan, P.S. Raghavan and P. Ramasamy, Effect of EDTA on the metastable zone width of ADP 213 (2000) 389
Ramasamy, P., see Rajesh, N.P. 213 (2000) 389
Rauls, M., K. Bartosch, M. Kind, St. Kuch, R. Lacmann and A. Mersmann, The influence of impurities on crystallization kinetics – a case study on ammonium sulfate 213 (2000) 116
Rechenberg, I., see Hofmann, L. 213 (2000) 229
Robey, H.F., S.Yu. Potapenko and K.D. Summerhays, "Bending" of steps on rapidly grown KH_2PO_4 crystals due to an inhomogeneous surface supersaturation field 213 (2000) 340
Robey, H.F. and S.Yu. Potapenko, Ex situ microscopic observation of the lateral instability of macrosteps on the surfaces of rapidly grown KH_2PO_4 crystals 213 (2000) 355
Rodriguez, M.E., O. Zelaya-Angel, J.J. Pérez Bueno, S. Jimenez-Sandoval and L. Tirado, Influence of Te inclusions and precipitates on the crystalline and thermal properties of CdTe single crystals 213 (2000) 259
Rudolph, P., see Frank, Ch. 213 (2000) 10

Sack-Kongehl, H., see Nepijko, S.A. 213 (2000) 129
Sakai, S., see Wang, T. 213 (2000) 188
Samanta, S.B., see Singh, R. 213 (2000) 70
Sanz-Hervás, A., see Villar, C. 213 (2000) 214
Schlögl, R., see Nepijko, S.A. 213 (2000) 129
Schultz, L., see Bitterlich, H. 213 (2000) 319
Sekiguchi, T., see Xia, Y. 213 (2000) 328
Semchinova, O., see Verozubova, G.A. 213 (2000) 334
Seo, K., see Oyama, Y. 213 (2000) 221
Shah, A.P., see Chandvankar, S.S. 213 (2000) 250
Shaji Kumar, M.D., M. Akaishi and S. Yamaoka, Formation of diamond from supercritical H_2O–CO_2 fluid at high pressure and high temperature 213 (2000) 203
Sharma, B.B., see Chandvankar, S.S. 213 (2000) 250

Sharma, T.K., M.R. Gokhale and B.M. Arora, Long-wavelength photoluminescence from InGaP/GaAs heterointerfaces grown by metal organic vapour-phase epitaxy 213 (2000) 241
Sharma, T.K., see Chandvankar, S.S. 213 (2000) 250
Shen, B., see Chen, P. 213 (2000) 27
Shih, H.C., see Wen, C.-Y. 213 (2000) 150
Silvestre, C.L., see Jernigan, G.G. 213 (2000) 299
Singh, R., S.B. Samanta, A.V. Narlikar and G.C. Trigunayat, A combined optical, SEM and STM study of growth spirals on the polytypic cadmium iodide crystals 213 (2000) 70
Srinivasan, K., see Rajesh, N.P. 213 (2000) 389
Su, C.-H., M.A. George, W. Palosz, S. Feth and S.L. Lehoczky, Contactless growth of ZnSe single crystals by physical vapor transport 213 (2000) 267
Su, G., S., Y. He, Z. Li, R. Jiang, C. Zhu, S. Yang, Directional solution growth of cylindrical α-$NiSO_4 \cdot 6H_2O$ crystal 213 (2000) 99
Suk, M.-J. and K. Leonartz, Halo growth during unidirectional solidification of camphor–naphthalene eutectic system 213 (2000) 141
Sukiasyan, R.P., see Petrosyan, A.M. 213 (2000) 103
Summerhays, K.D., see Robey, H.F. 213 (2000) 340
Sun, L., M. Akaishi and S. Yamaoka, Formation of diamond in the system of Ag_2CO_3 and graphite at high pressure and high temperatures 213 (2000) 411
Sun, L., see Zhang, S. 213 (2000) 415
Suto, K., see Oyama, Y. 213 (2000) 221

Taishi, T., see Huang, X. 213 (2000) 283
Talyzin, A.V., L.-E. Tergenius and U. Jansson, Single- crystal growth of $C_{70}S_8$ – a new phase in the C_{70}–sulphur system 213 (2000) 63
Tergenius, L.-E., see Talyzin, A.V. 213 (2000) 63
Terzyan, S.S., see Petrosyan, A.M. 213 (2000) 103
Thompson, P.E., see Jernigan, G.G. 213 (2000) 299
Tirado, L., see Rodriguez, M.E. 213 (2000) 259
Tönhardt, R. and G. Amberg, Dendritic growth of randomly oriented nuclei in a shear flow 213 (2000) 161
Trigunayat, G.C., see Singh, R. 213 (2000) 70
Tsamouras, D., see Pierri, E. 213 (2000) 93
Twigg, M.E., see Jernigan, G.G. 213 (2000) 299

Uffmann, D., see Verozubova, G.A. 213 (2000) 334

Vaccaro, P.O., see Villar, C. 213 (2000) 214
Verma, D., see Chandvankar, S.S. 213 (2000) 250
Verozubova, G.A., A.I. Gribenyukov, V.V. Korotkova, O. Semchinova and D. Uffmann, Synthesis and growth of $ZnGeP_2$ crystals for nonlinear optical applications 213 (2000) 334
Villar, C., A. Sanz-Hervás, M. Aguilar, P.O. Vaccaro, E.J. Abril, M. López and K. Fujita, High-resolution X-ray diffraction study of $AlAs/Al_{0.5}Ga_{0.5}As/GaAs$ quantum well structures grown by molecular beam epitaxy on (1 1 *n*)A GaAs 213 (2000) 214
Voliotis, V., see Wang, X.-L. 213 (2000) 19

Wagener, M.C., J.R. Botha and A.W.R. Leitch, Characterization of secondary phases formed during MOVPE growth of InSbBi mixed crystals 213 (2000) 51
Wang, H., see Li, D. 213 (2000) 308
Wang, M., see Chen, P. 213 (2000) 27
Wang, Q., see Li, D. 213 (2000) 308
Wang, T., Y. Morishima, N. Naoi and S. Sakai, A new method for a great reduction of dislocation density in a GaN layer grown on a sapphire substrate 213 (2000) 188
Wang, X.D., see Liu, H.Y. 213 (2000) 193
Wang, X.-L., V. Voliotis, R. Grousson and M. Ogura, Improved heterointerface quality of V-shaped AlGaAs/GaAs quantum wires characterized by atomic force microscopy and microphotoluminescence 213 (2000) 19
Wang, Z.G., see Liu, H.Y. 213 (2000) 193
Watanabe, K. and M. Mizoguchi, Ice configuration near a growing ice lens in a freezing porous medium consisting of micro glass particles 213 (2000) 135
Wen, C.-Y., X.J. Guo, J.H. Huang and H.C. Shih, Determination of the three-dimensional crystallographic misorientation in heterostructures by selected area diffraction (SAD) in cross-sectional TEM 213 (2000) 150
Weyers, M., see Hofmann, L. 213 (2000) 229
Wu, F., see Hayakawa, Y. 213 (2000) 40
Wu, J., see Liu, H.Y. 213 (2000) 193
Wu, J., see Fan, T.W. 213 (2000) 276
Wu, W., see Xia, Y. 213 (2000) 328
Wu, X.S., see Chen, P. 213 (2000) 27

Xia, Y., T. Sekiguchi, W. Zhang, X. Jiang, W. Wu and T. Yao, Effects of hydrogen ion bombardment and boron doping on (0 0 1) polycrystalline diamond films 213 (2000) 328
Xie, S.Y., see Chen, P. 213 (2000) 27
Xie, X., see Hayakawa, Y. 213 (2000) 40
Xu, B., see Liu, H.Y. 213 (2000) 193
Xu, T., see Cao, Y.G. 213 (2000) 198
Xu, Y.P., see Cao, Y.G. 213 (2000) 198

Yamaguchi, T., see Hayakawa, Y. 213 (2000) 40
Yamaoka, S., see Shaji Kumar, M.D. 213 (2000) 203
Yamaoka, S., see Sun, L. 213 (2000) 411
Yang, C.S., see Lee, J.J. 213 (2000) 33
Yang, M., see Kim, C. 213 (2000) 235
Yang, S., see Su, G. 213 (2000) 99
Yang-Bitterlich, W., see Bitterlich, H. 213 (2000) 319
Yao, T., see Xia, Y. 213 (2000) 328
Yi, J., see Kim, C. 213 (2000) 235
Yonenaga, I., see Huang, X. 213 (2000) 283
Yoo, H.-D., see Hwang, D.-H. 213 (2000) 57
Yoo, T.-K., see Kim, C. 213 (2000) 235
Yu, J., see Li, D. 213 (2000) 308
Yu, Z., see Li, D. 213 (2000) 308
Yuan, B., see Hayakawa, Y. 213 (2000) 40
Yuan, J., see Fan, T.W. 213 (2000) 276

Zeimer, U., see Hofmann, L. 213 (2000) 229
Zelaya-Angel, O., see Rodriguez, M.E. 213 (2000) 259
Zhang, C., see Li, D. 213 (2000) 308
Zhang, L., S.L. Gu, T.F. Kuech and M.P. Boleslawski, Gallium nitride growth using diethyl gallium chloride as an alternative gallium source 213 (2000) 1
Zhang, R., see Chen, P. 213 (2000) 27
Zhang, S., Z. Cheng, S. Zhang, J. Han, L. Sun and H. Chen, Growth and non-critical phase-matching third-harmonic-generation of $Gd_xY_{1-x}Ca_4O(BO_3)_3$ crystal 213 (2000) 415
Zhang, S., see Zhang, S. 213 (2000) 415
Zhang, W., see Xia, Y. 213 (2000) 328
Zheng, Y.D., see Chen, P. 213 (2000) 27
Zhong, X., see Hayakawa, Y. 213 (2000) 40
Zhou, Y.G., see Chen, P. 213 (2000) 27
Zhu, C., see Su, G. 213 (2000) 99
Zhu, J.M., see Chen, P. 213 (2000) 27

ELSEVIER

Journal of Crystal Growth 213 (2000) 426–427

JOURNAL OF CRYSTAL GROWTH

www.elsevier.nl/locate/jcrysgro

Subject index

Apparatus
- for industrial crystallization 116

Computer simulation
- of dendritic growth 161
- of multiply twinned particles 129
- of vertical zone melting growth 395
Convection 161, 395

Diodes, see Device characterization
Device characterization
- diodes 241
- heterojunctions 33, 241
- lasers 241
- quantum wells 19, 214, 241
- quantum wires and dots 193

Epitaxy, see Thin film growth
Etching
- chemical 276, 328
Eutectic growth
- of camphor naphthalene 141

Heat flow control
- of growing ice particles 125
- of melt grown gallium arsenide 10
- of vertical zone melting growth 395
Heterojunctions, see Device characterization
Hydrodynamics, see Convection

Kinetics
- of growth 51, 70, 75, 93, 112, 116, 141, 368
- of interface control 75
- of nucleation 93, 116, 157, 259
- of spontaneous precipitation 381

Lasers, see Device characterization
Lasers, crystals for
- potassium dihydrogen phosphate 340
- zinc germanium phosphide 334

Melt growth technique
- by Bridgman–Stockbarger method
- - of aluminum gallium antimonide 207
- - of zinc germanium phosphide 334
- by Czochralski method
- - of gadolinium yttrium calcium borate 415
- - of gallium arsenide 10
- - of silicon 57, 283
- by dendritic web
- - of silicon 288
- by floating zone method
- - of $Tb_{0.4}Y_{0.6}Ni_2B_2C$ 319
Microgravity, growth under
- of indium gallium antimonide 40
Morphological stability
- of potassium dihydrogen phosphate 355

Nucleation
- of diamond 203, 328, 411
Numbers
- Rayleigh 395

Quantum wells, see Device characterization
Quantum wires and dots, see Device characterization

Solution growth technique
- by aqueous solution
- - of arginine phosphate monohydrate 103
- by electrolytic method
- - of zirconium titanate 112
- by hydrothermal growth
- - of aluminum nitride 198
- by low temperature method
- - of ammonium dihydrogen ortho phosphate 389
- - of carbon sulphur 63
- - of magnesium ammonium phosphate 381
- - of nickel sulphate hexahydrate 99
- by slow evaporation
- - of cadmium iodide 70
Superconductivity materials, high T_c
- - $REBa_2Cu_3O_{7-\delta}$ 312
- - $Tb_{0.4}Y_{0.6}Ni_2B_2C$ 319
Superlattices, multilayers
- of germanium silicon 308
Surface structure

0022-0248/00/$ - see front matter © 2000 Elsevier Science B.V. All rights reserved.
PII: S0022-0248(00)00477-2

- of cadmium iodide crystals 70
- of multiply twinned particles 129
- of potassium dihydrogen phosphate 340, 355

Thin film growth, epitaxy
- by atomic layer epitaxy
- - of gallium arsenide 221
- by liquid phase epitaxy
- - of indium thallium phosphide 250
- by molecular beam epitaxy
- - of aluminum arsenide 214
- - of aluminum gallium arsenide 214
- - of gallium arsenide 193, 214
- - of gallium nitride 33
- - of indium aluminum arsenide 193
- - of indium arsenide 193
- - of silicon germanium 299
- by vapor phase epitaxy
- - through chemical vapor deposition
- - - of gallium nitride 235
- - - of silicon germanium 308
- - through metalorganic chemical vapor deposition
- - - of aluminum gallium arsenide 19, 229
- - - of gallium arsenide 241
- - - of gallium nitride 1, 27, 188
- - - of indium antimonide bismide 51
- - - of indium gallium phosphide 241
- - theory of misorientation in heterostructures 150

Vapor growth technique
- by chemical vapor deposition
- - of diamond 79
- - of gold 83
- by evaporation and condensation
- - of zinc selenide 267
- - of gallium nitride 408

Vapor–liquid–solid growth
- of indium bismuth 51